

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

EMH2314 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1= $28m\Omega$ (typ.)
- · 1.8V drive
- · Halogen free compliance
- · Protection Diode in

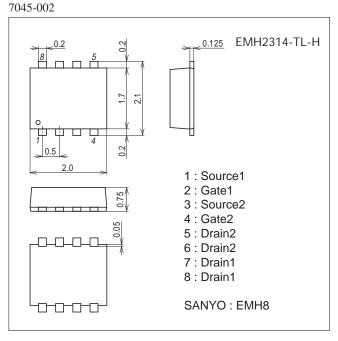
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-20	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.0	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit: mm (typ.)



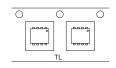
Product & Package Information

• Package : EMH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

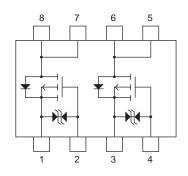
Taping Type: TL



Marking



Electrical Connection

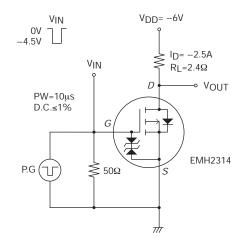


EMH2314

Electrical Characteristics at Ta=25°C

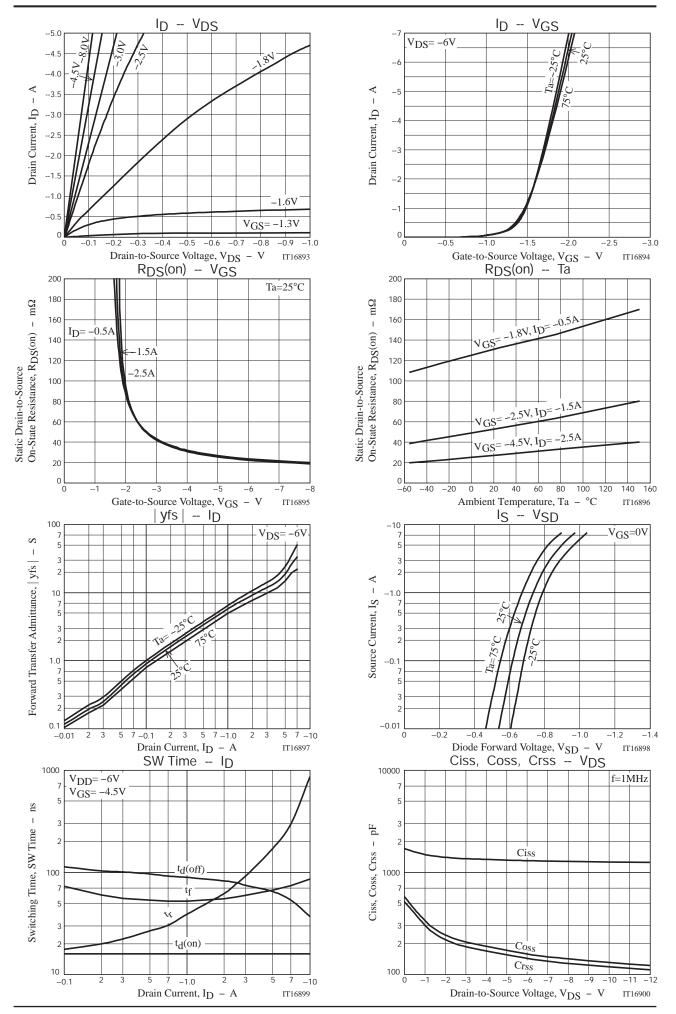
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Syllibol	Conditions	min.	typ.	max.	Uill	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID= -1mA, VGS=0V	-12			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} = -12V, V _{GS} =0V			-10	μΑ	
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} = -6V, I _D = -1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V _D S= -6V, I _D = -2.5A		11		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D = -2.5A, V _G S= -4.5V		28	37	mΩ	
	R _{DS} (on)2	I _D = -1.5A, V _G S= -2.5V		53	75	mΩ	
	R _{DS} (on)3	I _D = -0.5A, V _G S= -1.8V		133	200	mΩ	
Input Capacitance	Ciss			1300		pF	
Output Capacitance	Coss	V _{DS} = -6V, f=1MHz		158		pF	
Reverse Transfer Capacitance	Crss			143		pF	
Turn-ON Delay Time	t _d (on)			16		ns	
Rise Time	t _r	Considered Total Circuit		77		ns	
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		79		ns	
Fall Time	tf			58		ns	
Total Gate Charge	Qg			12		nC	
Gate-to-Source Charge	Qgs	V _{DS} = -6V, V _{GS} = -4.5V, I _D = -5A		3		nC	
Gate-to-Drain "Miller" Charge	Qgd			2		nC	
Diode Forward Voltage	V _{SD}	I _S = -5A, V _{GS} =0V		-0.9	-1.2	V	

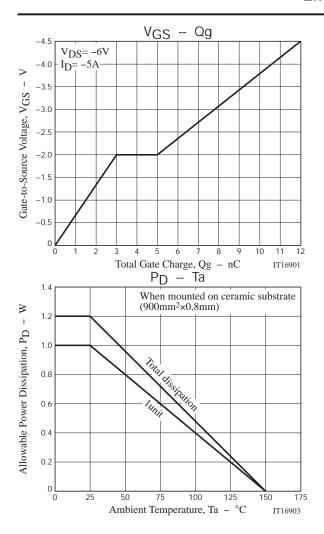
Switching Time Test Circuit

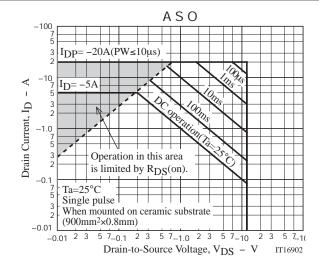


Ordering Information

Device	Package	Shipping	memo		
EMH2314-TL-H	MH2314-TL-H EMH8		Pb Free and Halogen Free		





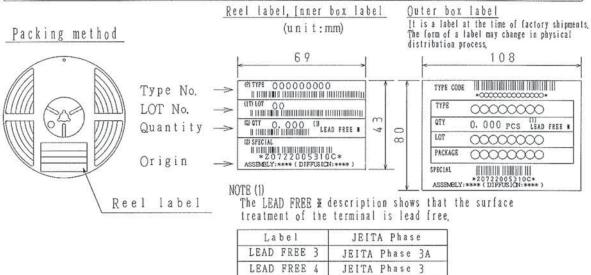


Embossed Taping Specification

EMH2314-TL-H

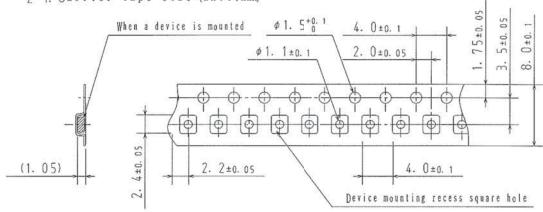
1. Packing Format

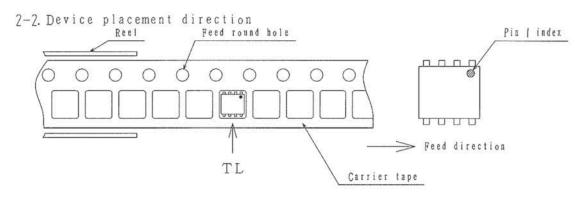
Package Name Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format		
	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
ЕМН8	MCP4	3, 000	15, 000	90, 000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) $440 \times 195 \times 210$



2. Taping configuration

7-1. Carrier tape size (unit:mm)

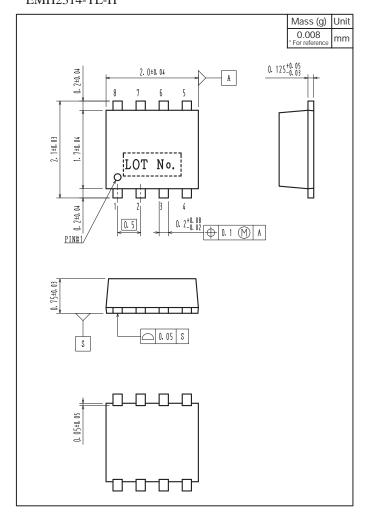




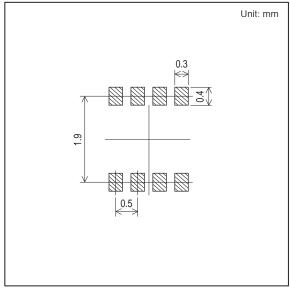
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH2314-TL-H



Land Pattern Example



Note on usage: Since the EMH2314 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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